

ABSTRACT OF THE DISCLOSURE

A semiconductor device and method of adding metal layers in a semiconductor device with signal reallocation are disclosed. The device has a first layer with a plurality of signal wires. A second layer adjacent to the first layer is also included that has a plurality of signal wires. The signal wires in the first and second layers are substantially parallel with each other. The signal wires are distributed between the first and second layer in a manner that reduces the wire capacitance and/or resistance thereby permitting higher frequency operation and lower power consumption in the device.